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TITLE: SEMICONDUCTOR LASER

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ABSTRACT:

PROBLEM TO BE SOLVED: To suppress generation of cracks due to lattice mismatching, existing between a current constricting layer and an n-type layer by a method, where an AlGaN layer is deposited from the place separated further than by a specified distance from the contact surface of a substrate with a buffer layer at the film-forming temperature in a specific range between p-type electrodes.

SOLUTION: An AlN buffer layer 2, an n-type GaN layer 3, a low- temperature AlGaN intermediate layer 4 and an AlGaN current constricting layer 5, deposited at a film-forming temperature of 300 to 800

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